

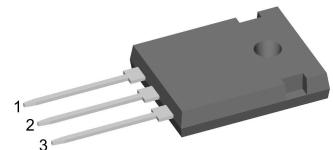
Thyristor

V_{RRM} = 1200 V
 I_{TAV} = 20 A
 V_T = 1.23 V

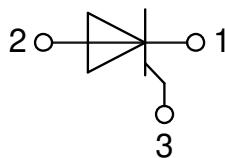
Single Thyristor

Part number

CS20-12io1



Backside: anode



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

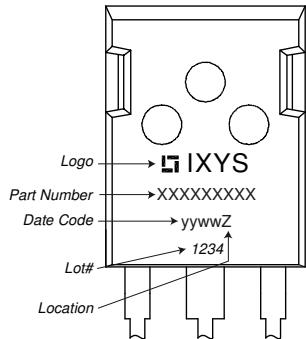
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Thyristor

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ\text{C}$			1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200 \text{ V}$ $V_{R/D} = 1200 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		20 2	μA mA
V_T	forward voltage drop	$I_T = 20 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$		1.27	V
		$I_T = 40 \text{ A}$			1.53	V
		$I_T = 20 \text{ A}$	$T_{VJ} = 125^\circ\text{C}$		1.23	V
		$I_T = 40 \text{ A}$			1.57	V
I_{TAV}	average forward current	$T_C = 130^\circ\text{C}$	$T_{VJ} = 150^\circ\text{C}$		20	A
$I_{T(RMS)}$	RMS forward current	180° sine			31	A
V_{T0}	threshold voltage	$\left. \begin{array}{l} \text{slope resistance} \\ \end{array} \right\} \text{for power loss calculation only}$	$T_{VJ} = 150^\circ\text{C}$		0.87	V
r_T	slope resistance				17.3	$\text{m}\Omega$
R_{thJC}	thermal resistance junction to case				0.6	K/W
R_{thCH}	thermal resistance case to heatsink			0.3		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		200	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$		260	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		280	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ\text{C}$		220	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		240	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$		340	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		325	A^2s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$	$T_{VJ} = 150^\circ\text{C}$		240	A^2s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$V_R = 0 \text{ V}$		240	A^2s
C_J	junction capacitance	$V_R = 400 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	16		pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu\text{s}$	$T_C = 150^\circ\text{C}$		10	W
		$t_p = 300 \mu\text{s}$			5	W
P_{GAV}	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ\text{C}; f = 50 \text{ Hz}$ repetitive, $I_T = 60 \text{ A}$			150	$\text{A}/\mu\text{s}$
		$t_p = 200 \mu\text{s}; di_G/dt = 0.3 \text{ A}/\mu\text{s};$				
		$I_G = 0.3 \text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 20 \text{ A}$			500	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$		1000	$\text{V}/\mu\text{s}$
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$		1.3	V
			$T_{VJ} = -40^\circ\text{C}$		1.6	V
I_{GT}	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$		50	mA
			$T_{VJ} = -40^\circ\text{C}$		80	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ\text{C}$		0.2	V
I_{GD}	gate non-trigger current				5	mA
I_L	latching current	$t_p = 10 \mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		150	mA
		$I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$				
I_H	holding current	$V_D = 6 \text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ\text{C}$		100	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ\text{C}$		2	μs
		$I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$				
t_q	turn-off time	$V_R = 100 \text{ V}; I_T = 20 \text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ\text{C}$		150		μs
		$di/dt = 15 \text{ A}/\mu\text{s}$ $dv/dt = 20 \text{ V}/\mu\text{s}$ $t_p = 200 \mu\text{s}$				

Package TO-247

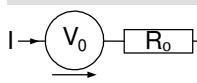
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_d	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

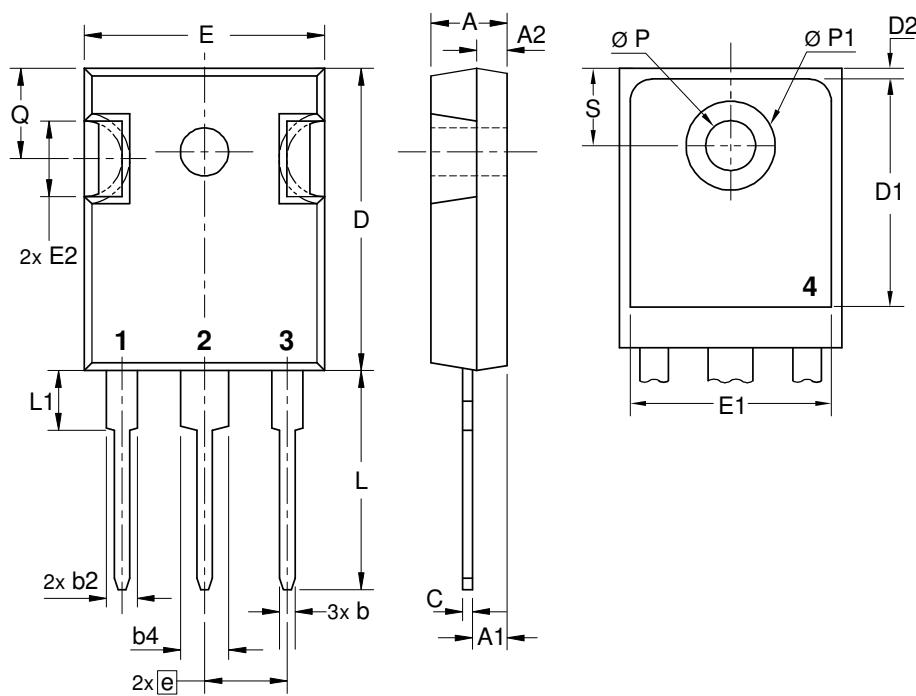
Product Marking


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CS20-12io1	CS20-12io1	Tube	30	466514

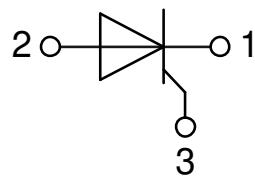
Similar Part	Package	Voltage class
CS20-14io1	TO-247AD (3)	1400
CS20-16io1	TO-247AD (3)	1600

Equivalent Circuits for Simulation
* on die level
 $T_{VJ} = 150^\circ\text{C}$

	Thyristor	
$V_{0\max}$	threshold voltage	0.87 V
$R_{0\max}$	slope resistance *	14.8 mΩ

Outlines TO-247


Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



Thyristor

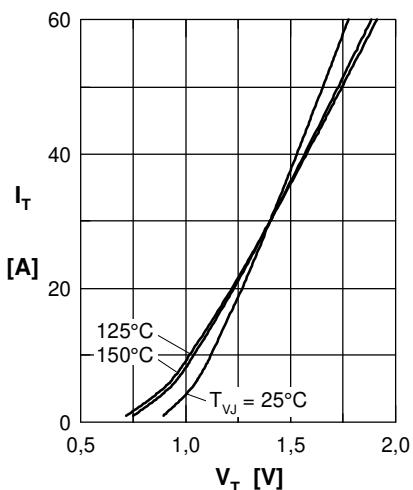


Fig. 1 Forward characteristics

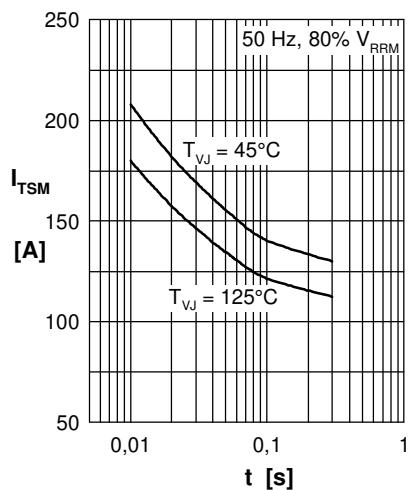


Fig. 2 Surge overload current

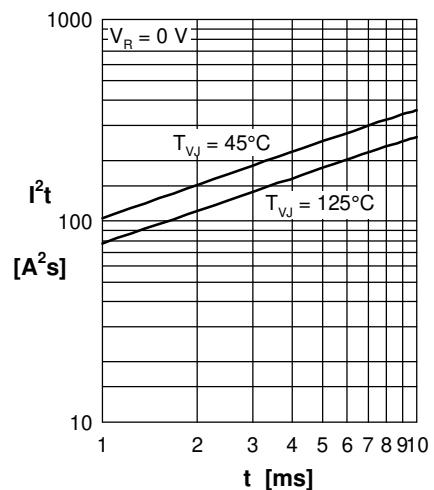


Fig. 3 I^2t versus time (1-10 ms)

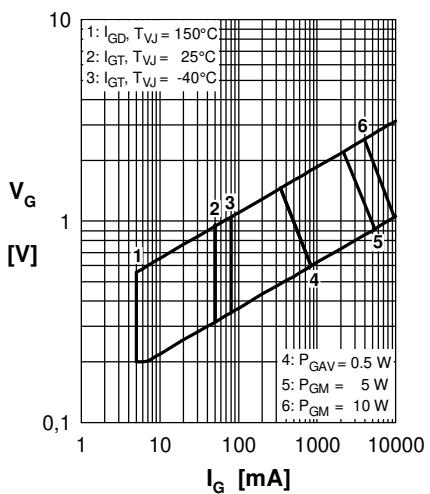


Fig. 4 Gate trigger characteristics

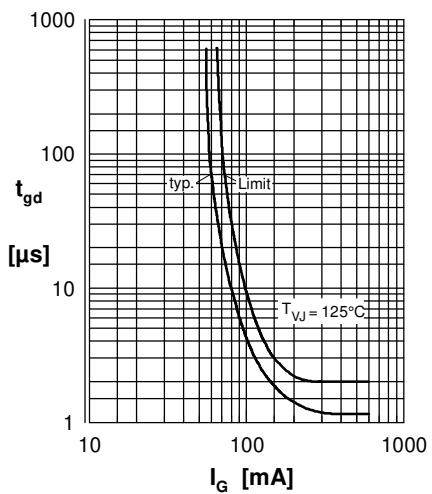


Fig. 5 Gate controlled delay time

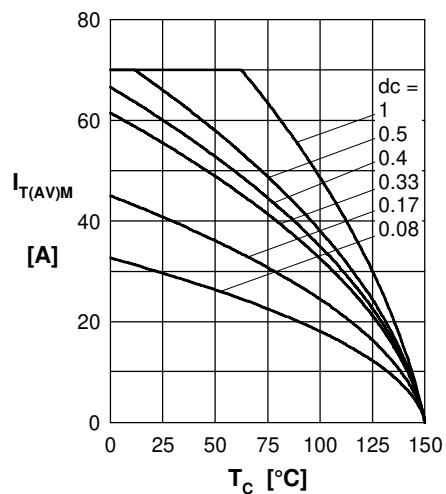


Fig. 6 Max. forward current at case temperature

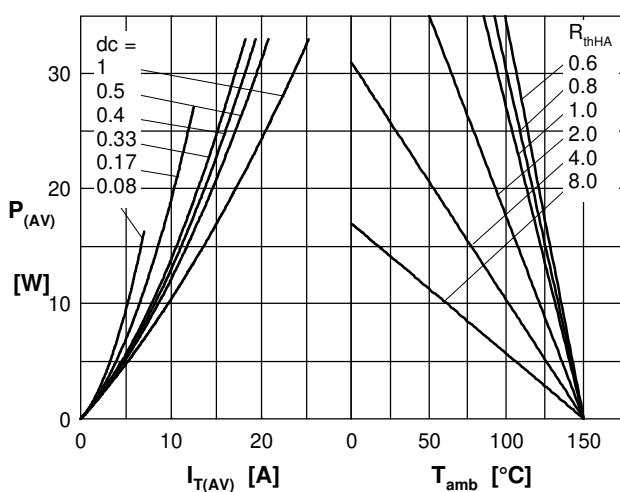


Fig. 7a Power dissipation versus direct output current
Fig. 7b and ambient temperature

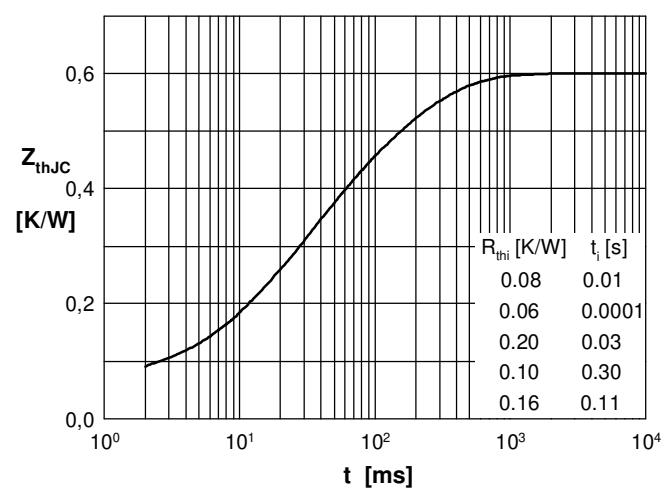


Fig. 8 Transient thermal impedance junction to case

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